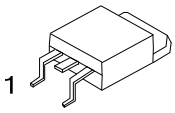
UF5N07

Power MOSFET

5A, 70V N-CHANNEL ENHANCEMENT MODE POWER MOSFET



TO-252

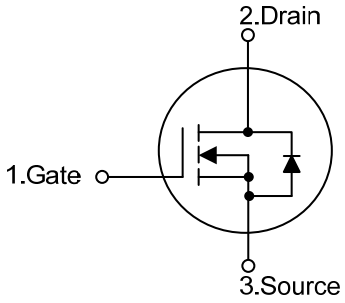
■ DESCRIPTION

The UTC **UF5N07** is a N-channel power MOSFET providing very low on-resistance. It has high efficiency and perfect cost-effectiveness. It can be generally applied in the commercial and industrial fields.

■ FEATURES

* $R_{DS(ON)}$ < 0.2Ω @ V_{GS} =10V, I_D =2.5A
* Simple drive requirement

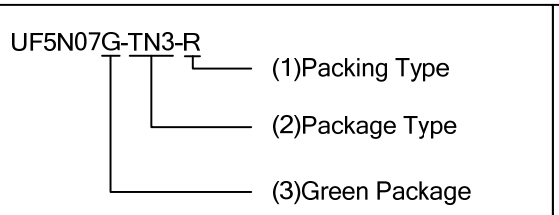
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF5N07L-TN3-R	UF5N07G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

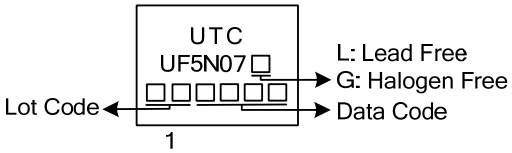


(1) R: Tape Reel

(2) TN3: TO-252

(3) G: Halogen Free and Lead Free L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATING (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	70	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	Continuous	I_D	5	A
	Pulsed (Note 2)	I_{DM}	15	A
Avalanche Energy (Note 3)	Single Pulsed (Note 3)	E_{AS}	11	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	18	V/ns
Power Dissipation		P_D	30	W
Junction Temperature		T_J	+150	°C
Storage Temperature Range		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 0.1 mH, I_{AS} = 15 A, V_{DD} = 50 V, R_G = 25 Ω, Starting T_J = 25°C.
4. I_{SD} ≤ 5.0 A, di/dt ≤ 200 A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J = 25°C.

■ THERMAL DATA

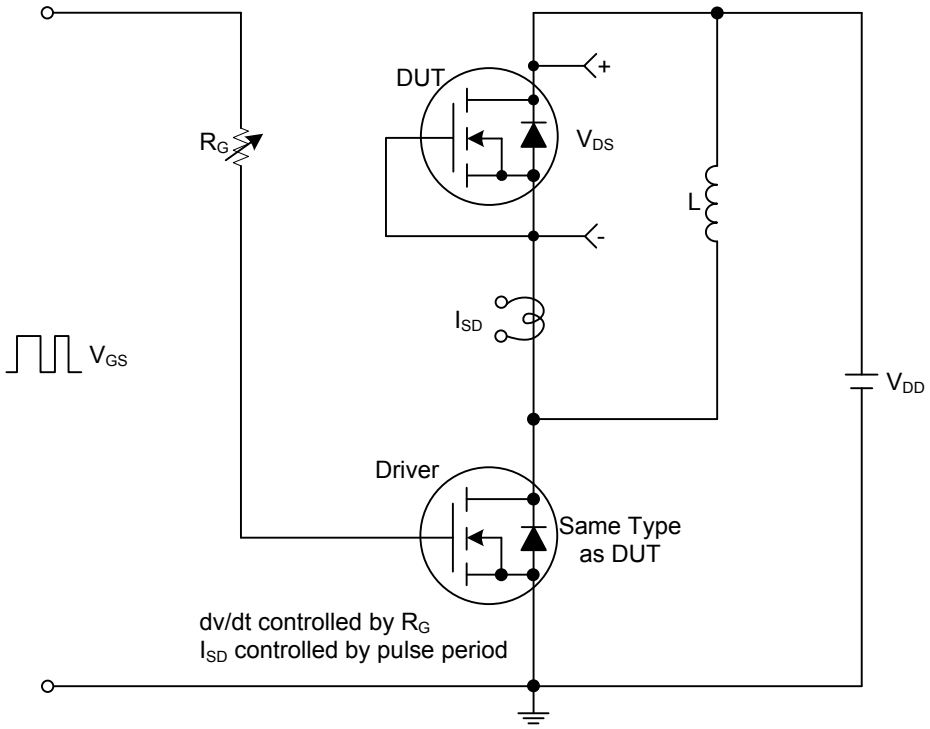
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{JC}	4.2	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

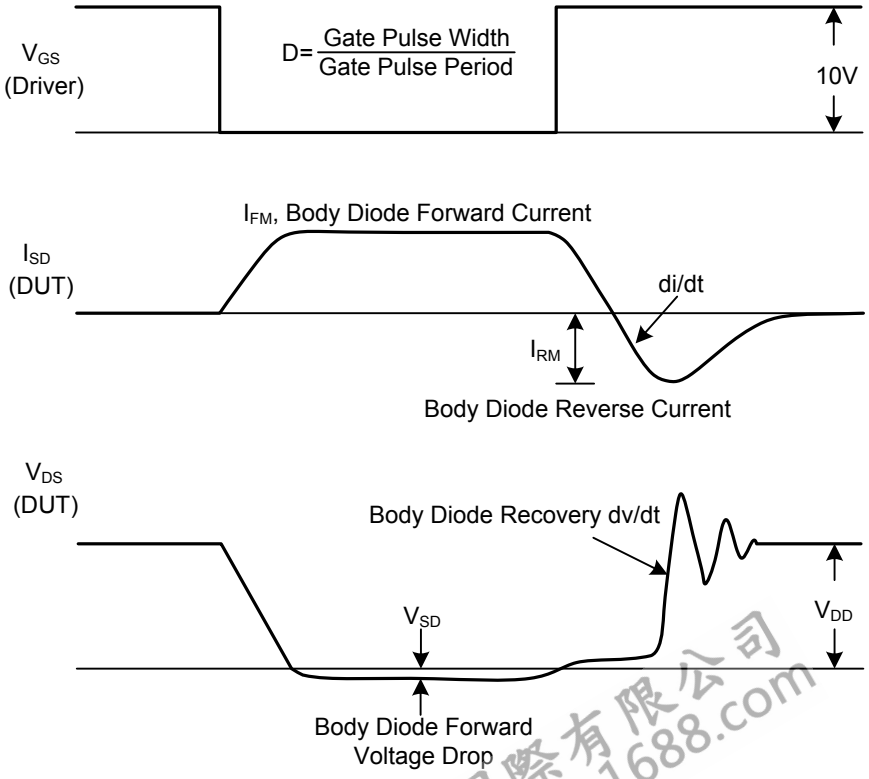
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} =0V, I_D =250μA	70			V
Drain-Source Leakage Current	I_{DSS}	V_{DS} =70V,V_{GS} =0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS} =±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} =V_{GS}, I_D =250μA	2.0		4.0	V
Drain to Source On-state Resistance	$R_{DS(ON)}$	V_{GS} =10V, I_D =2.5A			0.2	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{DS}=25V,V_{GS}=0V,f =1.0MHz		250		pF
Output Capacitance	C_{OSS}			55		pF
Reverse Transfer Capacitance	C_{RSS}			10		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=56V, V_{GS}=10V, I_D=5.0A, I_G=1mA (Note 1, 2)		11.3		nC
Gate Source Charge	Q_{GS}			5.8		nC
Gate Drain Charge	Q_{GD}			1.7		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=35V, V_{GS}=10V, I_D=5.0A, R_G =25Ω (Note 1, 2)		2.4		ns
Turn-ON Rise Time	t_R			15		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			3.4		ns
Turn-OFF Fall-Time	t_F			2.7		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				5	A
Maximum Body-Diode Pulsed Current	I_{SM}				15	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S =5.0A, V_{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	I_S=5.0A,V_{GS}=0V, dI/dt=100A/μs		40		ns
Reverse Recovery Charge	Q_{rr}			110		nC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS



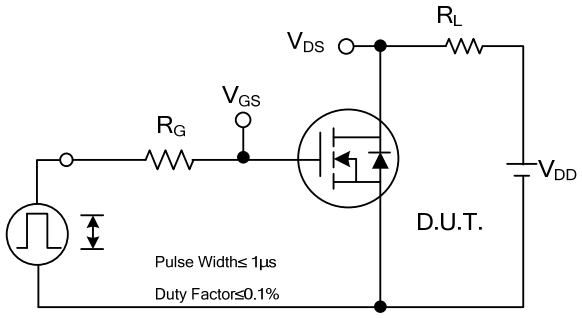
Peak Diode Recovery dv/dt Test Circuit



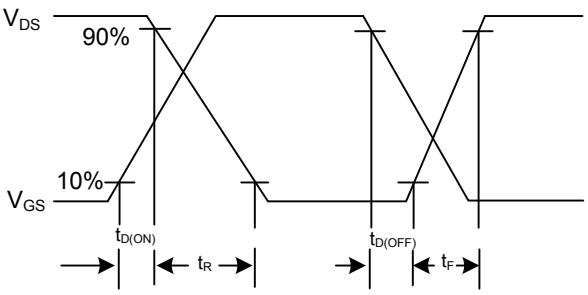
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

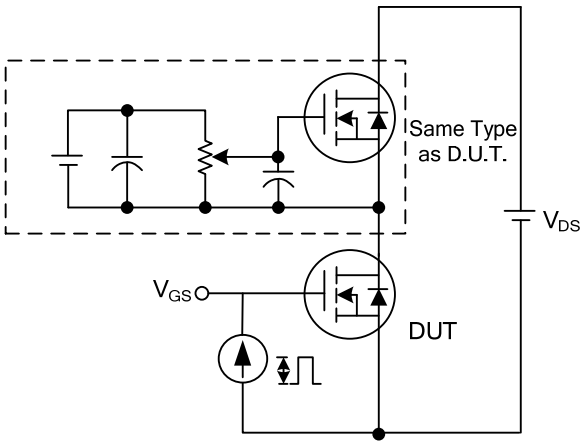
■ TEST CIRCUITS AND WAVEFORMS



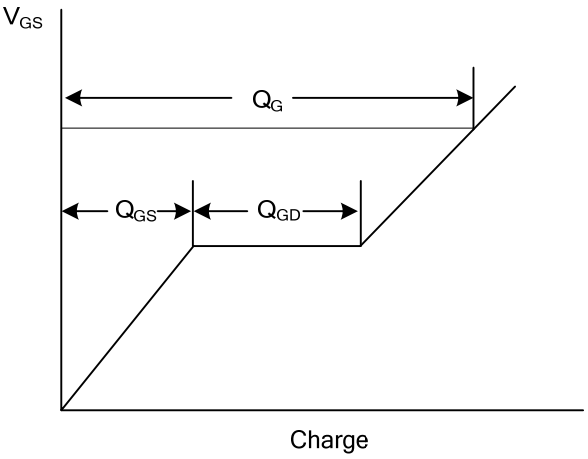
Switching Test Circuit



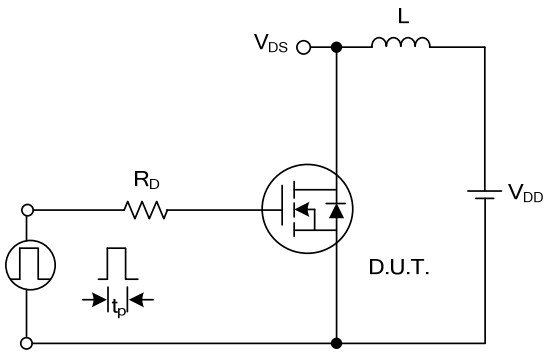
Switching Waveforms



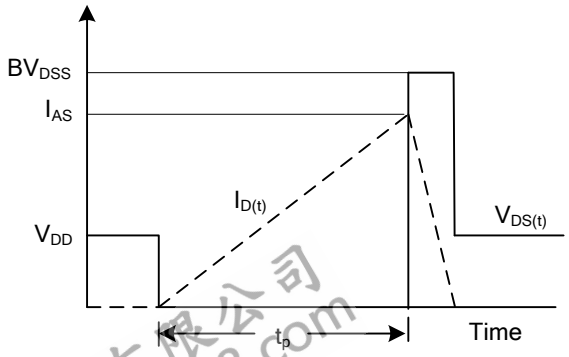
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS